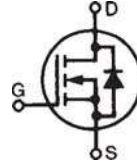
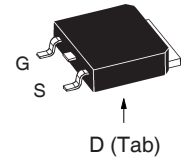
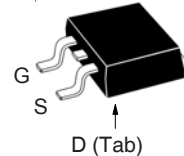
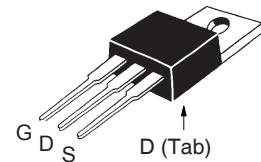


**Depletion Mode
MOSFET**
**IXTY08N100D2
IXTA08N100D2
IXTP08N100D2**
 $V_{DSX} = 1000V$
 $I_{D(on)} \geq 800mA$
 $R_{DS(on)} \leq 21\Omega$
N-Channel


Symbol	Test Conditions	Maximum Ratings	
V_{DSX}	$T_J = 25^\circ C$ to $150^\circ C$	1000	V
V_{GSX}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
P_D	$T_C = 25^\circ C$	60	W
T_J		- 55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		- 55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-252	0.35	g
	TO-263	2.50	g
	TO-220	3.00	g

TO-252 (IXTY)

TO-263 AA (IXTA)

TO-220AB (IXTP)


G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSX}	$V_{GS} = -5V, I_D = 25\mu A$	1000		V
$V_{GS(off)}$	$V_{DS} = 25V, I_D = 25\mu A$	- 2.0		V
I_{GSX}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 50 nA
$I_{DSX(off)}$	$V_{DS} = V_{DSX}, V_{GS} = -5V$ $T_J = 125^\circ C$			1 μA 15 μA
$R_{DS(on)}$	$V_{GS} = 0V, I_D = 400mA, \text{ Note 1}$			21 Ω
$I_{D(on)}$	$V_{GS} = 0V, V_{DS} = 50V, \text{ Note 1}$	800		mA

Features

- Normally ON Mode
- International Standard Packages
- Molding Epoxies Meet UL 94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Audio Amplifiers
- Start-up Circuits
- Protection Circuits
- Ramp Generators
- Current Regulators
- Active Loads

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 30\text{V}$, $I_D = 400\text{mA}$, Note 1	330	560	mS
C_{iss}	$V_{GS} = -10\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		325	pF
C_{oss}			24	pF
C_{rss}			6.5	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = \pm 5\text{V}$, $V_{DS} = 500\text{V}$, $I_D = 400\text{mA}$ $R_G = 10\Omega$ (External)		28	ns
t_r			57	ns
$t_{d(off)}$			34	ns
t_f			48	ns
$Q_{g(on)}$	$V_{GS} = 5\text{V}$, $V_{DS} = 500\text{V}$, $I_D = 400\text{mA}$		14.6	nC
Q_{gs}			1.2	nC
Q_{gd}			8.3	nC
R_{thJC}	TO-220			2.08 $^\circ\text{C/W}$
R_{thCS}			0.50	$^\circ\text{C/W}$

Safe-Operating-Area Specification

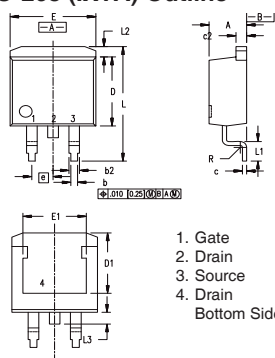
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 800\text{V}$, $I_D = 45\text{mA}$, $T_C = 75^\circ\text{C}$, $T_p = 5\text{s}$	36		W

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
V_{SD}	$I_F = 800\text{mA}$, $V_{GS} = -10\text{V}$, Note 1		0.8	1.3 V
t_{rr}	$I_F = 800\text{mA}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GS} = -10\text{V}$		1.03	μs
I_{RM}			7.40	A
Q_{RM}			3.80	μC

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

TO-263 (IXTA) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.40	0.74	.016	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	8.00	8.89	.280	.320
E	9.65	10.41	.380	.405
E1	6.22	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.13	0	.005

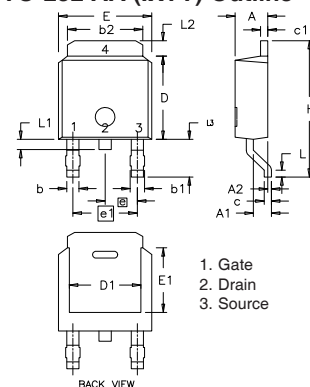
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

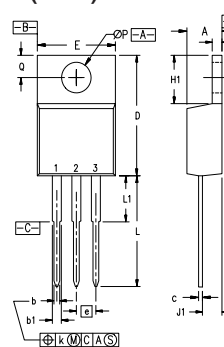
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-252 AA (IXTY) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.19	2.38	0.086	0.094
A1	0.89	1.14	0.035	0.045
A2	0	0.13	0	0.005
b	0.64	0.89	0.025	0.035
b1	0.76	1.14	0.030	0.045
b2	5.21	5.46	0.205	0.215
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.32	5.21	0.170	0.205
E	6.35	6.73	0.250	0.265
E1	4.32	5.21	0.170	0.205
e	2.28	BSC	0.090	BSC
e1	4.57	BSC	0.180	BSC
H	9.40	10.42	0.370	0.410
L	0.51	1.02	0.020	0.040
L1	0.64	1.02	0.025	0.040
L2	0.89	1.27	0.035	0.050
L3	2.54	2.92	0.100	0.115

TO-220 (IXTP) Outline



Pins: 1 - Gate
3 - Source
2 - Drain
4 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100	BSC	2.54	BSC
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

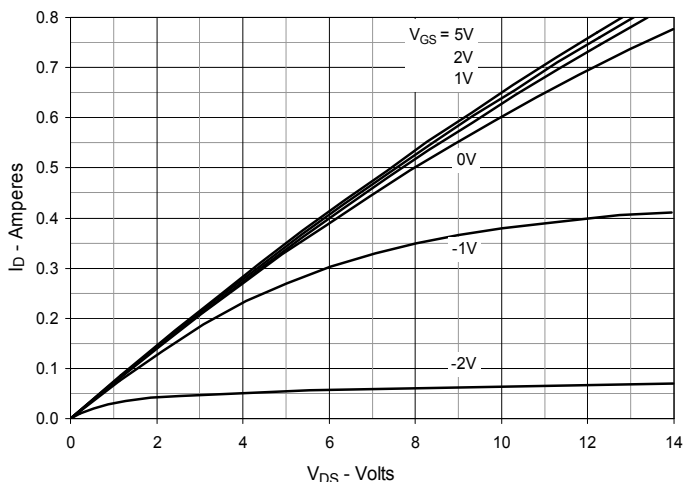


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

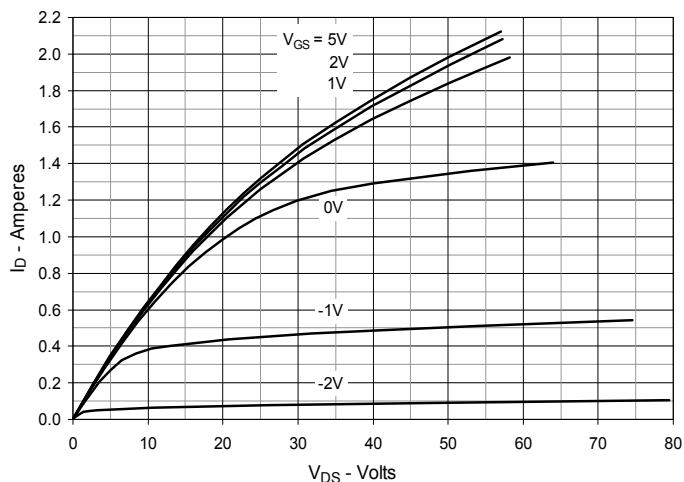


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

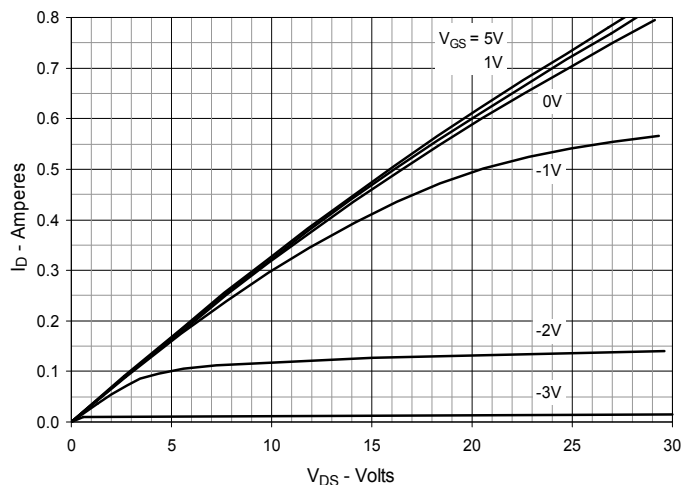


Fig. 4. Drain Current @ $T_J = 25^\circ\text{C}$

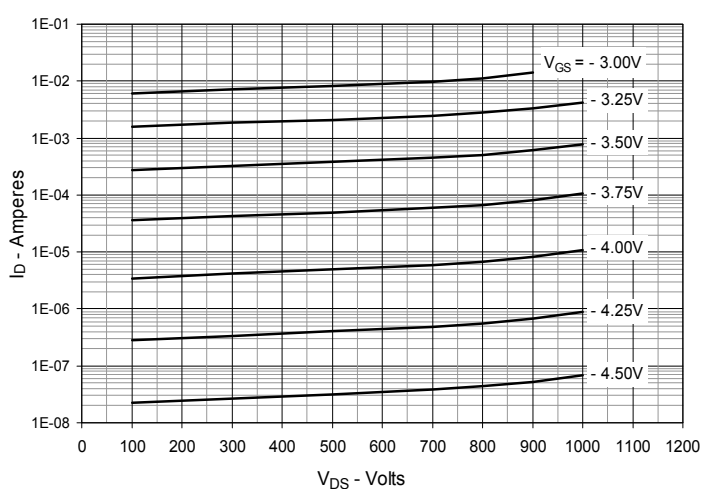


Fig. 5. Drain Current @ $T_J = 100^\circ\text{C}$

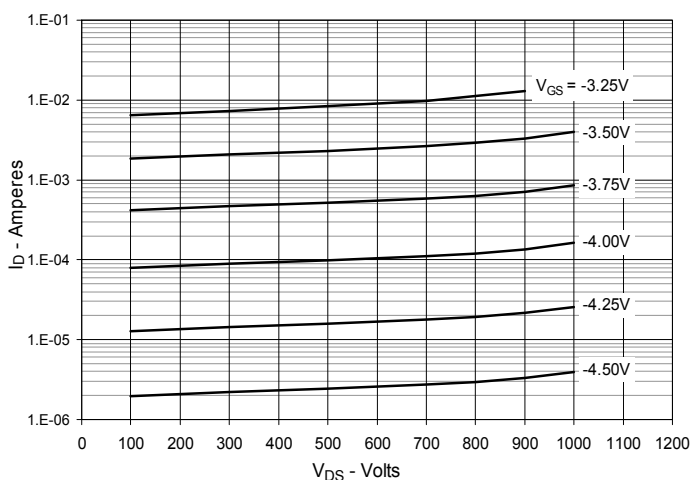


Fig. 6. Dynamic Resistance vs. Gate Voltage

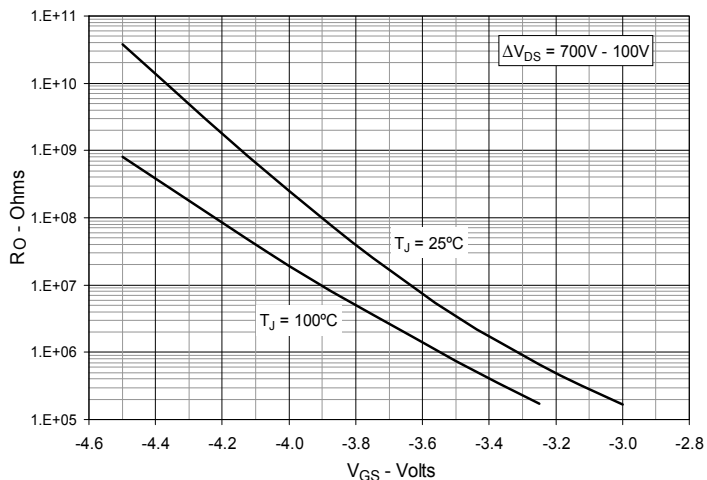


Fig. 7. Normalized $R_{DS(on)}$ vs. Junction Temperature

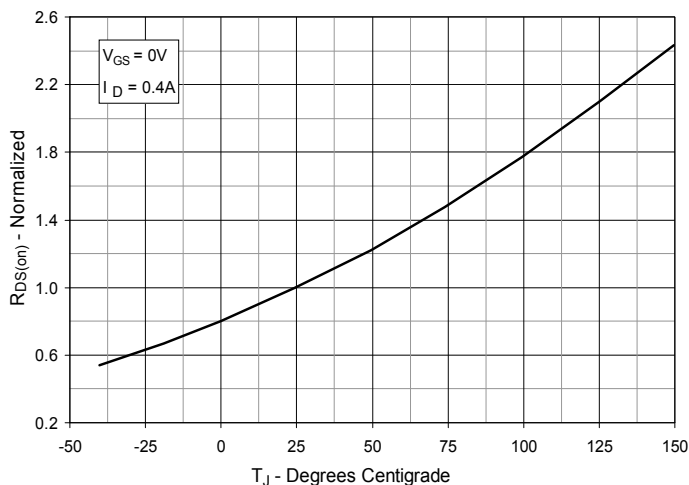


Fig. 8. $R_{DS(on)}$ Normalized to $I_D = 0.4A$ Value vs. Drain Current

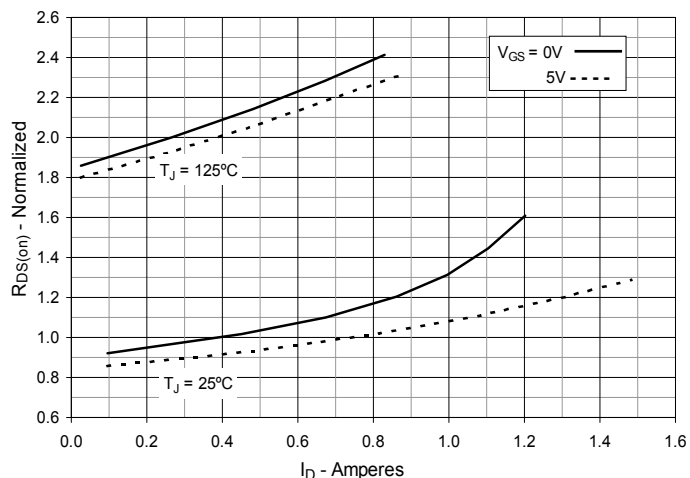


Fig. 9. Input Admittance

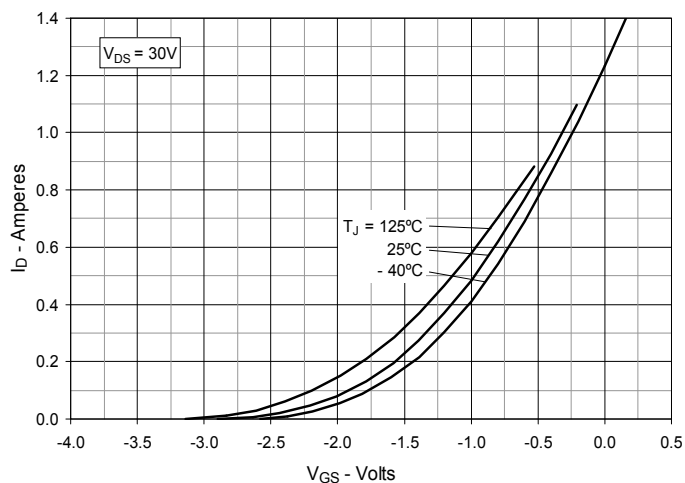


Fig. 10. Transconductance

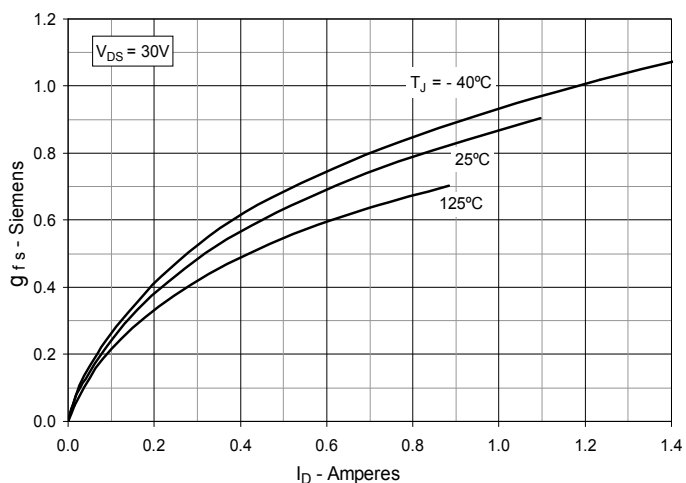


Fig. 11. Breakdown and Threshold Voltages vs. Junction Temperature

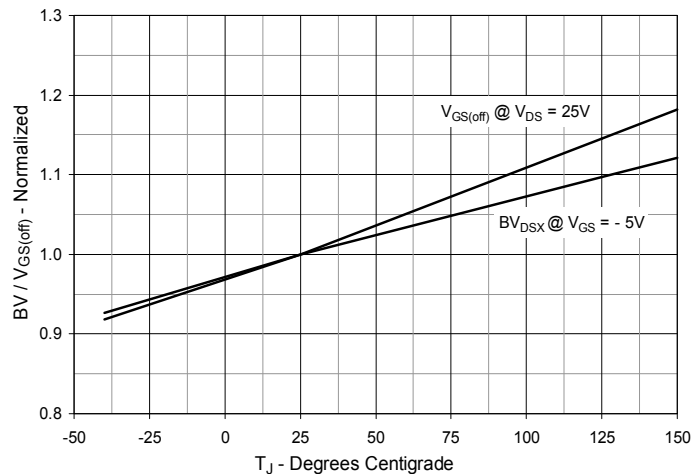


Fig. 12. Forward Voltage Drop of Intrinsic Diode

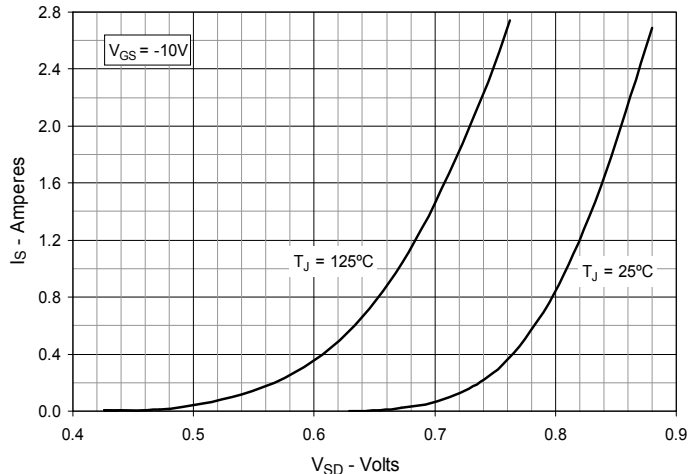


Fig. 13. Capacitance

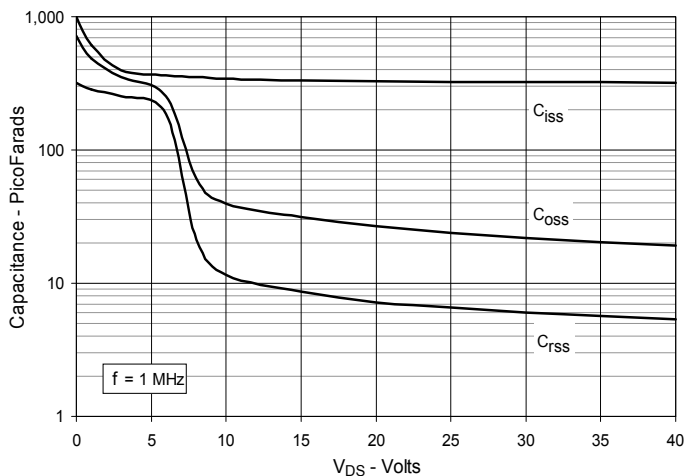


Fig. 14. Gate Charge

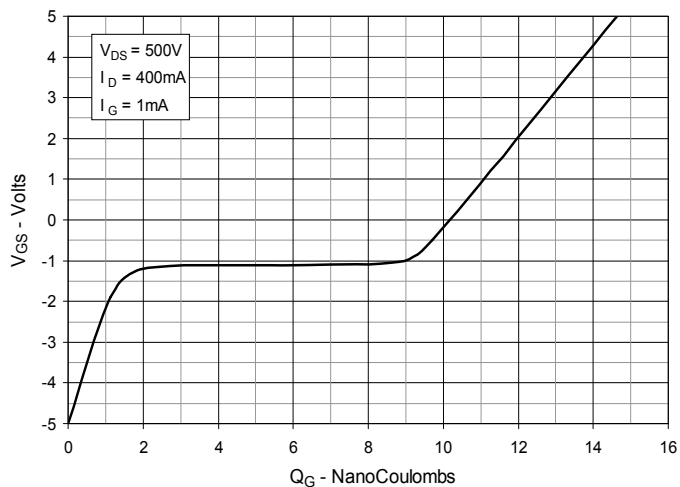


Fig. 15. Forward-Bias Safe Operating Area @ $T_C = 25^\circ\text{C}$

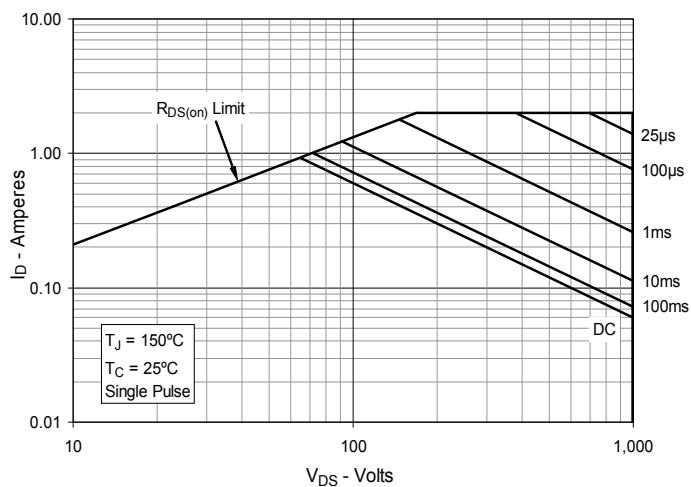


Fig. 16. Forward-Bias Safe Operating Area @ $T_C = 75^\circ\text{C}$

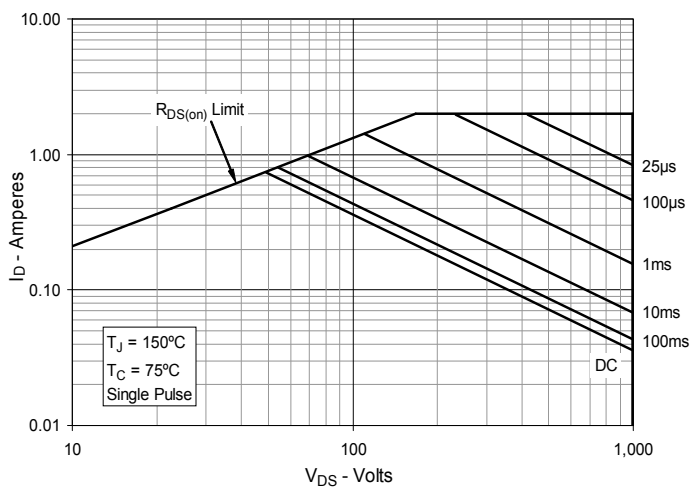


Fig. 17. Maximum Transient Thermal Impedance

